# NXP EC103D1W SCR datasheet

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Planar passivated ultra sensitive gate Silicon Controlled Rectifier in a SOT223 surface mountable plastic package.

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## 1. General description

Planar passivated ultra sensitive gate Silicon Controlled Rectifier in a SOT223 surface mountable plastic package.

## 2. Features and benefits

- Planar passivated for voltage ruggedness and reliability
- Ultra sensitive gate
- Surface mountable package

# 3. Applications

- Electronic ballasts
- Safety shut down and protection circuits
- Sensing circuits
- Smoke detectors
- Switched Mode Power Supplies

## 4. Quick reference data

Table 1. C	Quick reference data					
Symbol	Parameter	Conditions	Mi	n <b>Typ</b>	Мах	Unit
V <sub>DRM</sub>	repetitive peak off- state voltage		-	-	400	V
V <sub>RRM</sub>	repetitive peak reverse voltage		-	-	400	V
I <sub>TSM</sub>	non-repetitive peak on- state current	half sine wave; $T_{j(init)} = 25 \text{ °C}$ ; $t_p = 10 \text{ ms}$ ; <u>Fig. 4</u> ; <u>Fig. 5</u>	-	-	8	A
Tj	junction temperature		-	-	125	°C
I <sub>T(RMS)</sub>	RMS on-state current	half sine wave; T <sub>sp</sub> ≤ 114 °C; <u>Fig. 2;</u> <u>Fig. 3</u>	-	-	0.8	A
Static char	acteristics					
I <sub>GT</sub>	gate trigger current	V <sub>D</sub> = 12 V; I <sub>T</sub> = 0.1 A; T <sub>j</sub> = 25 °C; <u>Fig. 9</u>	-	3	12	μA





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Symbol	Parameter	Conditions		Min	Тур	Мах	Unit
Dynamic characteristics							
dV <sub>D</sub> /dt	rate of rise of off-state voltage	$V_{DM}$ = 268 V; T <sub>j</sub> = 125 °C; (V <sub>DM</sub> = 67% of V <sub>DRM</sub> ); exponential waveform; gate open circuit		-	150	-	V/µs

# 5. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	К	cathode	4	А – 🛃 - К
2	А	anode		G sym037
3	G	gate		, , , , , , , , , , , , , , , , , , ,
4	mb	mounting base; connected to anode	☐1	

# 6. Ordering information

Table 3. Ordering in	formation		
Type number	Package		
	Name	Description	Version
EC103D1W	SC-73	plastic surface-mounted package with increased heatsink; 4 leads	SOT223

## 7. Marking

Table 4. Marking codes	
Type number	Marking code
EC103D1W	WYM-103D1W

# 8. Limiting values

### Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

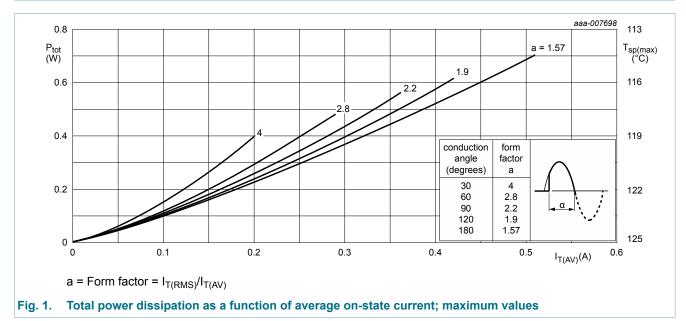
Symbol	Parameter	Conditions		Min	Max	Unit
V <sub>DRM</sub>	repetitive peak off-state voltage			-	400	V
V <sub>RRM</sub>	repetitive peak reverse voltage			-	400	V
I <sub>T(AV)</sub>	average on-state current	half sine wave; T <sub>sp</sub> ≤ 114 °C; <u>Fig. 1</u>		-	0.5	А
I <sub>T(RMS)</sub>	RMS on-state current	half sine wave; T <sub>sp</sub> ≤ 114 °C; <u>Fig. 2;</u> <u>Fig. 3</u>		-	0.8	A
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Symbol	Parameter	Conditions	Min	Max	Unit
I <sub>TSM</sub>	non-repetitive peak on-state current	half sine wave; T <sub>j(init)</sub> = 25 °C; t <sub>p</sub> = 10 ms; <u>Fig. 4; Fig. 5</u>	-	8	A
		half sine wave; T <sub>j(init)</sub> = 25 °C; t <sub>p</sub> = 8.3 ms	-	9	A
l <sup>2</sup> t	I <sup>2</sup> t for fusing	t <sub>p</sub> = 10 ms; sine-wave pulse	-	0.32	A <sup>2</sup> s
dl <sub>T</sub> /dt	rate of rise of on-state current	$I_T = 2 \text{ A}; I_G = 0.01 \text{ A}; dI_G/dt = 0.1 \text{ A}/\mu\text{s}$	-	50	A/µs
I <sub>GM</sub>	peak gate current		-	1	А
V <sub>RGM</sub>	peak reverse gate voltage		-	5	V
$P_{GM}$	peak gate power		-	2	W
P <sub>G(AV)</sub>	average gate power	over any 20 ms period	-	0.1	W
T <sub>stg</sub>	storage temperature		-40	150	°C
Tj	junction temperature		-	125	°C



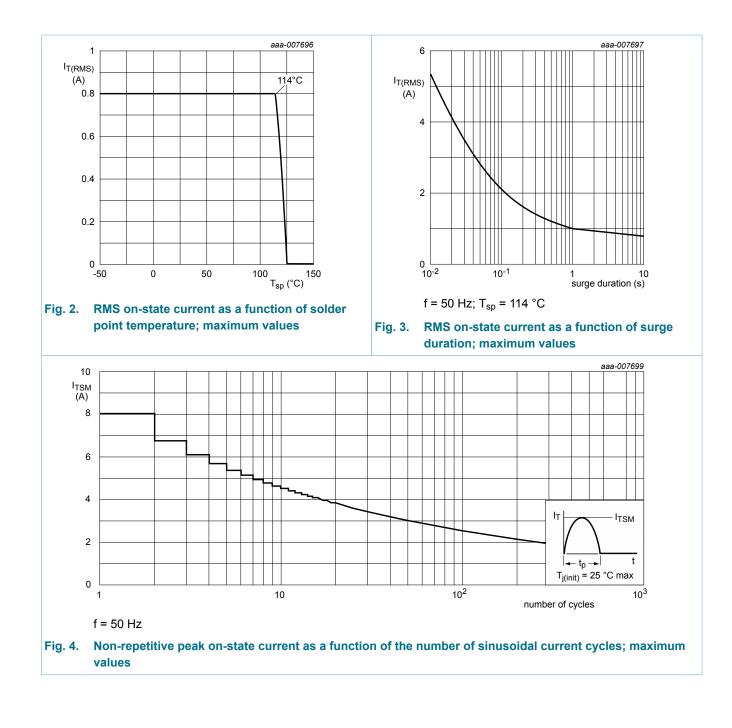
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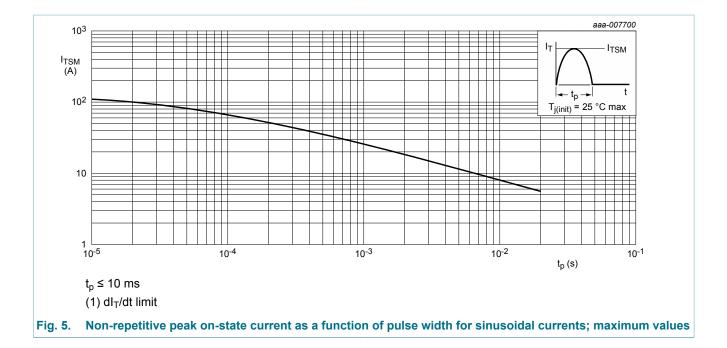
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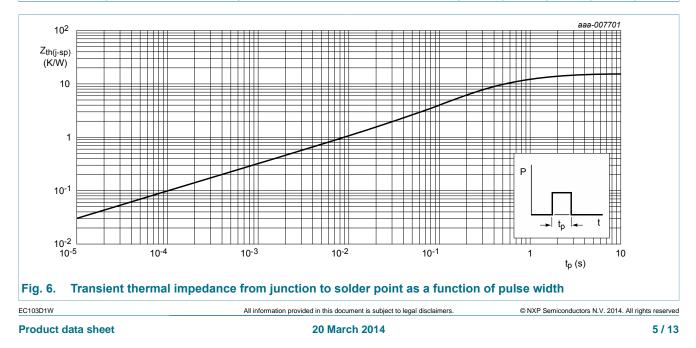
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# 9. Thermal characteristics

Table 6.	Thermal characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R <sub>th(j-sp)</sub>	thermal resistance from junction to solder point	Fig. 6	-	-	15	K/W
ui(j-a)	thermal resistance from junction to	printed circuit board mounted; minimum pad area; in free air; Fig. 7	-	70	-	K/W
	ambient	printed circuit board mounted; minimum footprint; in free air; Fig. 8	-	156	-	K/W

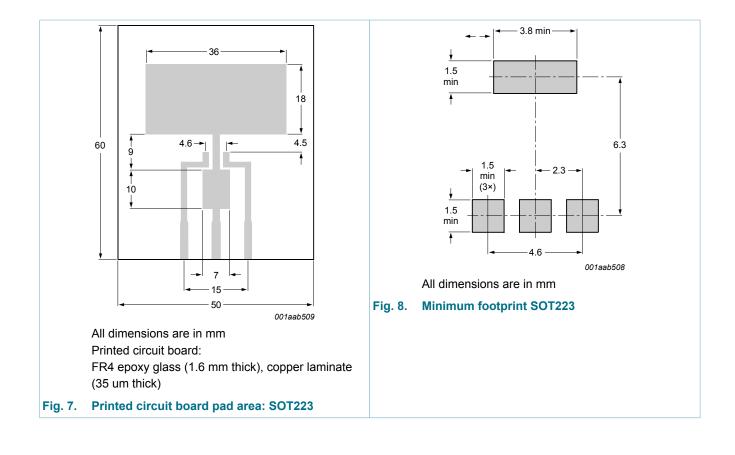


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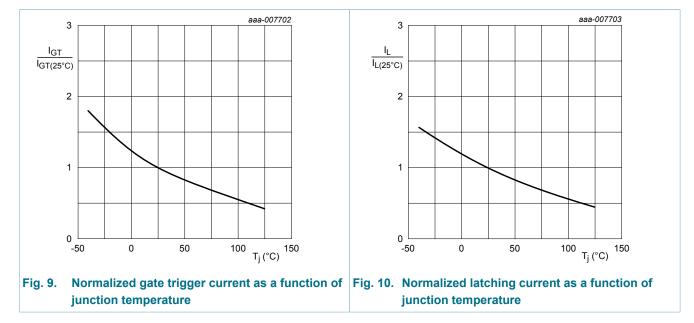


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# **10. Characteristics**

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics	· · ·				
I <sub>GT</sub>	gate trigger current	$V_D$ = 12 V; I <sub>T</sub> = 0.1 A; T <sub>j</sub> = 25 °C; <u>Fig. 9</u>	-	3	12	μA
IL	latching current	V <sub>D</sub> = 12 V; I <sub>G</sub> = 0.1 A; T <sub>j</sub> = 25 °C; Fig. 10	-	2	6	mA
I <sub>H</sub>	holding current	V <sub>D</sub> = 12 V; T <sub>j</sub> = 25 °C; <u>Fig. 11</u>	-	2	5	mA
V <sub>T</sub>	on-state voltage	I <sub>T</sub> = 1 A; T <sub>j</sub> = 25 °C; <u>Fig. 12</u>	-	1.2	1.35	V
V <sub>GT</sub>	gate trigger voltage	V <sub>D</sub> = 12 V; I <sub>T</sub> = 0.1 A; T <sub>j</sub> = 25 °C; Fig. 13	-	0.5	0.8	V
		V <sub>D</sub> = 400 V; I <sub>T</sub> = 0.1 A; T <sub>j</sub> = 125 °C; Fig. 13	0.2	0.3	-	V
ID	off-state current	V <sub>D</sub> = 400 V; T <sub>j</sub> = 125 °C	-	0.05	0.1	mA
I <sub>R</sub>	reverse current	V <sub>R</sub> = 400 V; T <sub>j</sub> = 125 °C	-	0.05	0.1	mA
Dynamic cł	naracteristics	· · · · ·	I	1	1	
dV <sub>D</sub> /dt	rate of rise of off-state voltage	$V_{DM}$ = 268 V; T <sub>j</sub> = 125 °C; (V <sub>DM</sub> = 67% of V <sub>DRM</sub> ); exponential waveform; gate open circuit	-	150	-	V/µs



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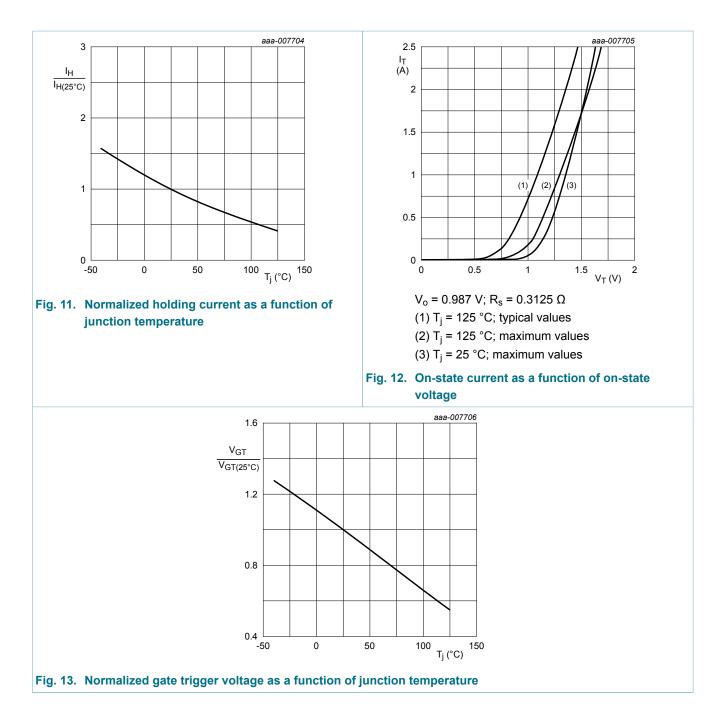
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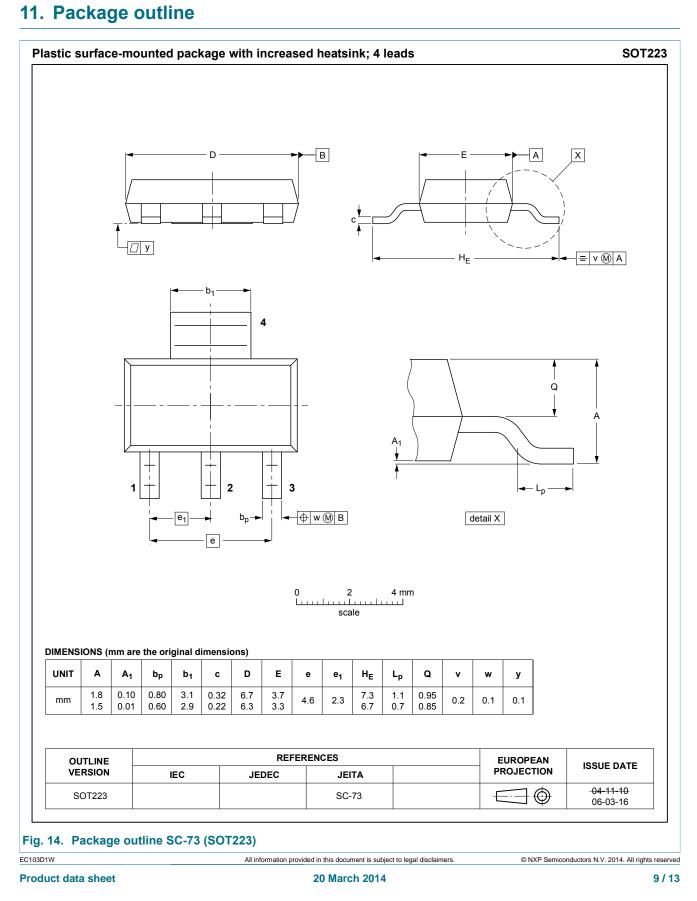


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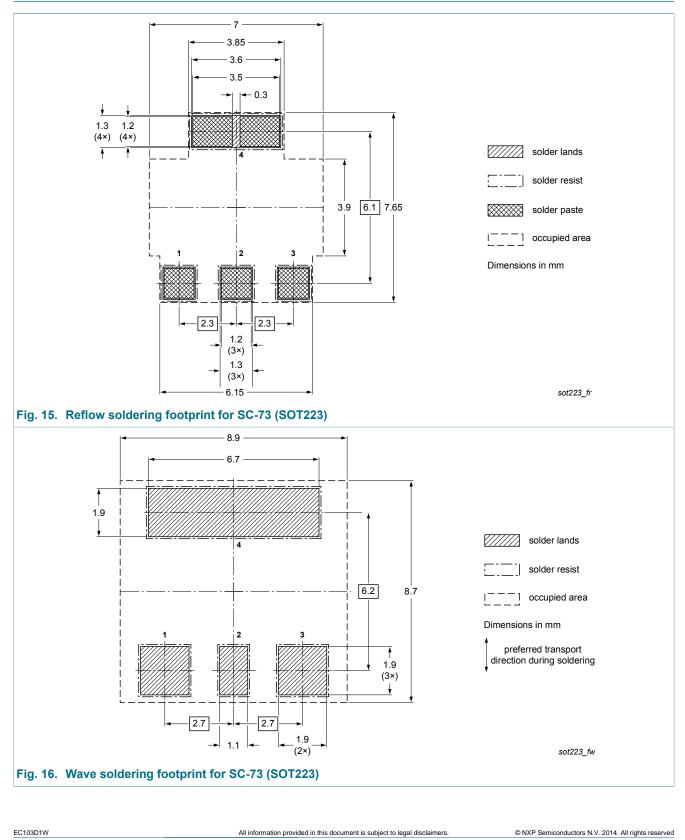
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## 12. Soldering



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## 13. Legal information

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Document status [1][2]	Product status [ <u>3]</u>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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